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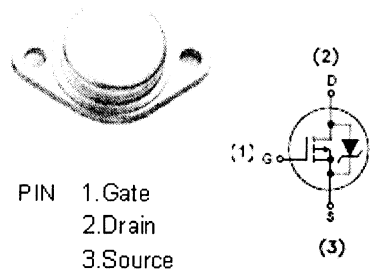
P-Channel MOSFET Transistor 2N6898

DESCRIPTION

- SOA is power-dissipation limited
- Nanosecond switching speeds
- Linear transfer characteristics
- High input impedance
- Majority carrier device

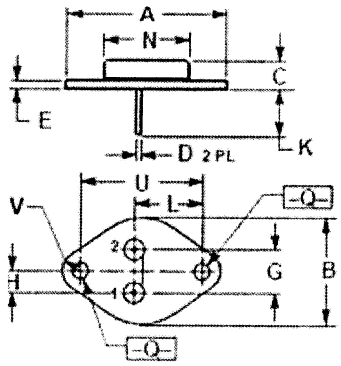


PIN 1.Gate
2.Drain
3.Source

TO-3 package

APPLICATIONS

- The 2N6898 is designed for application such as switching regulators,switching converters,motor drivers, relay drivers and drivers for high-power bipolar switching transistors requiring high speed and low gate-driver power



DIM	mm MIN	mm MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=37℃	-25	A
P_{tot}	Total Dissipation@TC=25℃	150	W
T_j	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.83	℃/W

Quality Semi-Conductors

• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= -1mA	-100		V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= -0.25mA	-1.5	-3	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= -10V; I_D= -15.8A		0.2	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= -20V;V_{DS}= 0		-100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -80V,V_{GS}= 0		-1	uA
V_{SD}	Diode Forward Voltage	I_F= -25A;V_{GS}= 0		1.6	V